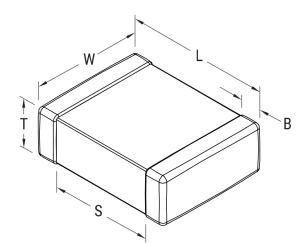


C0805C103J5RECTU

Aliases (C0805C103J5REC7800)

ESD SMD Comm X7R, Ceramic, 0.01 uF, 5%, 50 VDC, X7R, SMD, MLCC, Temperature Stable, Electro Static Discharge, Class II, 0805



Click here for the 3D model.

Dimensions	
Chip Size	0805
L	2mm +/-0.2mm
W	1.25mm +/-0.2mm
Т	0.78mm +/-0.10mm
S	0.75mm MIN
В	0.5mm +/-0.25mm

Packaging Specifications Packaging

PackagingT&R, 180mm, Paper TapePackaging Quantity4000

General Information Series ESD SMD Comm X7R Style SMD Chip SMD, MLCC, Temperature Stable, Electro Static Description Discharge, Class II Features Temperature Stable, Class II RoHS Yes Termination Tin Marking No AEC-Q200 No Component 11 mg Weight Shelf Life 78 Weeks MSL 1

Specifications		
Capacitance	0.01 uF	
Measurement Condition	1 kHz 1.0Vrms	
Capacitance Tolerance	5%	
Voltage DC	50 VDC	
ESD Level per AEC-Q200	25,000 V ESD Level	
Dielectric Withstanding Voltage	125 VDC	
Temperature Range	-55/+125°C	
Temperature Coefficient	X7R	
Capacitance Change with Reference to +25°C and 0 VDC Applied (TCC)	15%, 1kHz 1.0Vrms	
Dissipation Factor	2.5%1kHz1.0Vrms	
Aging Rate	3% Loss/Decade Hour: Referee Time is 1000 Hours	
Insulation Resistance	100 GOhms	

Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute - and we specifically disclaim - any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.

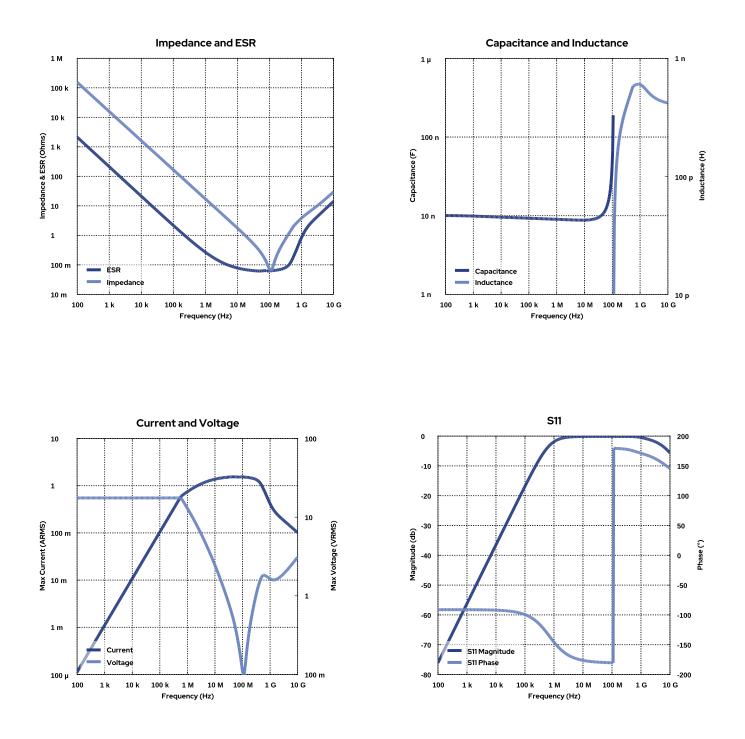


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ESD SMD Comm X7R, Ceramic, 0.01 uF, 5%, 50 VDC, X7R, SMD, MLCC, Temperature Stable, Electro Static Discharge, Class II, 0805

Simulations

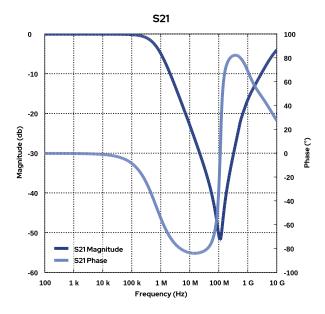
For the complete simulation environment please visit K-SIM.

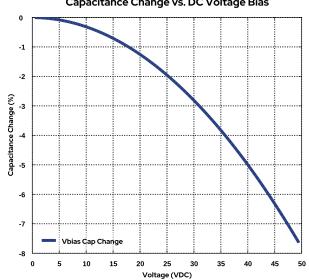




C0805C103J5RECTU Aliases (C0805C103J5REC7800)

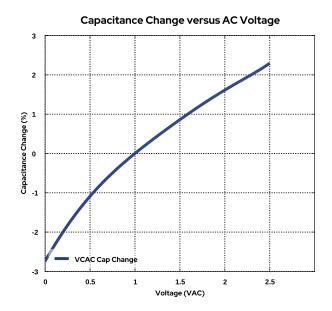
ESD SMD Comm X7R, Ceramic, 0.01 uF, 5%, 50 VDC, X7R, SMD, MLCC, Temperature Stable, Electro Static Discharge, Class II, 0805





Capacitance Change versus Temperature 2 0 -2 Capacitance Change (%) -4 -6 -8 -10 -12 Temp Çap Change -14 -60 -40 -20 0 20 40 60 80 100 120 140

Temperature (C)



Capacitance Change vs. DC Voltage Bias



C0805C103J5RECTU

Aliases (C0805C103J5REC7800)

ESD SMD Comm X7R, Ceramic, 0.01 uF, 5%, 50 VDC, X7R, SMD, MLCC, Temperature Stable, Electro Static Discharge, Class II, 0805

These are simulations.

This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.
- The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
- The effects shown herein are based on measured data from a multiple part sample of the parts in question.
- Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance. The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages generated at any other
- harmonics
- Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

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If you have any questions please contact K-SIM.

单击下面可查看定价,库存,交付和生命周期等信息

>>KEMET(基美)